

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	3	substrate adj10 (comprise or comprises or comprising) adj10 (silicon/germanium)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:54
2	BRS	L2	3743	(dielectric adj3 layer) adj10 (silicon adj3 dioxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:55
3	BRS	L6	342	si/sige	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:56
4	BRS	L7	0	(form or forms or formed or forming) adj10 (silicon adj3 dioxide) adj10 (SiGe or (silicon adj3 germanium)) adj10 (thermal\$3 adj3 oxida\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
5	BRS	L8	34	si/sige adj3 heterostructure	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57

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6	BRS	L11	14	substrate same (silicon/germanium adj3 alloy)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
7	BRS	L3	2	(dielectric adj3 layer) adj10 (silicon adj3 dioxide) same ((heterostructure adj3 bipolar adj3 transistor) or HBT)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
8	BRS	L4	11	(dielectric adj3 layer) adj10 (silicon adj3 dioxide) and ((heterostructure adj3 bipolar adj3 transistor) or HBT)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
9	BRS	L5	2	((dielectric adj3 layer) adj10 (silicon adj3 dioxide) and ((heterostructure adj3 bipolar adj3 transistor) or HBT)) and (thermal adj3 oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
10	BRS	L9	2	(si/sige adj3 heterostructure) same ((dielectric or (silicon adj3 dioxide)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57

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11	BRS	L10	2	(substrate adj10 (silicon/germanium adj3 alloy))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
12	BRS	L12	5	(substrate same (silicon/germanium adj3 alloy)) same (dielectric)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 16:57
13	BRS	L13	43	(silicon/germanium) adj3 alloy	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 17:22
14	BRS	L14	35	13 and (substrate or substrates)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 17:22
15	BRS	L15	15	13 same (substrate or substrates)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 17:42

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	56	(heterostructure) adj10 ((silicon adj3 germanium) or (SiGe))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/10/03 17:43